Patent Application 10/010,162

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Fwu-luan Ilshich et al.

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Scrial No.:

10/010,162

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Filed:

November 20, 2001

Title:

Method Of Forming Narrow Trenches In Semiconductor Substrates

Art Unit:

2812

Examiner:

Angel Roman

Docket No.: GS 149

Commissioner for Patents

PO Box 1450

Alexandria, VA 22313-1450

## PETITION UNDER 37 CFR 1.136(a) and RESPONSE TO FINAL OFFICE ACTION

Applicants hereby petition the Assistant Commissioner to grunt a one month extension of time, up to and including Tuesday, May 31, 2005 (May 28, 2005, being a Saturday, and Monday, May 30, 2005 being a l'ederal Holiday), in which to respond to the Office Action dated January 28, 2005 in the above-identified application. The extension fee may be charged to deposit account No. 50-1047. In addition, any deficiencies may be charged to deposit account No. 50-1047.

In response to the Office Action dated January 28, 2005, the period therefore having been extended by a Petition therefore and payment of the extension fee, kindly consider the following remarks.

Certificate of Facsimile Transmission

I hereby certify that this document and any document referenced herein has been transmitted via facsimile to the U.S. Patent and Trademark Office at (703) 872-9306

on May 31, 2005.

95/14/2005 DSASFAT 00000001 501047 100 Sale Ref: 00000001 DAM: 501047 1001012 10010152 01 FC:1251 120.00 DA

Karin L. Williams, Reg. No. 36,72

(Printed Name of Person Mailing Correspondence)

(Signature)